XL-ITR9608

技术数据表 Technical Data Sheet

特点（Characteristic）：

*

High reliability　High radiant intensity

电性参数

Electrical Characteristics

✧极限参数 =25 ：Absolute Maximum Ratings (Temperature=25ÁC):

Parameter		Symbol	Ratings	Unit
Input Emitter	Power Dissipation*1	PD	75	mW
	Continuous Forward Current	IF	50	mA
	Peak Forward Current*2	IF	1	A
	Reverse Voltage	VR	5	V
Output Detector	Power Dissipation*1	PD	75	mW
	- Collector-Emitter Voltage	VCEO	35	V
	- Emitter-Collector Voltage	VECO	5	V
	Collector Current	IC(on)	20	mA
Operating Temperature		Topr	-20~+85	
Storage Temperature		Tstg	-40~+85	
Lead Soldering Temperature*3		Tsol	260	

=25℃）：

Electro-Optical Charasteristics (Temperature=25ÁC):

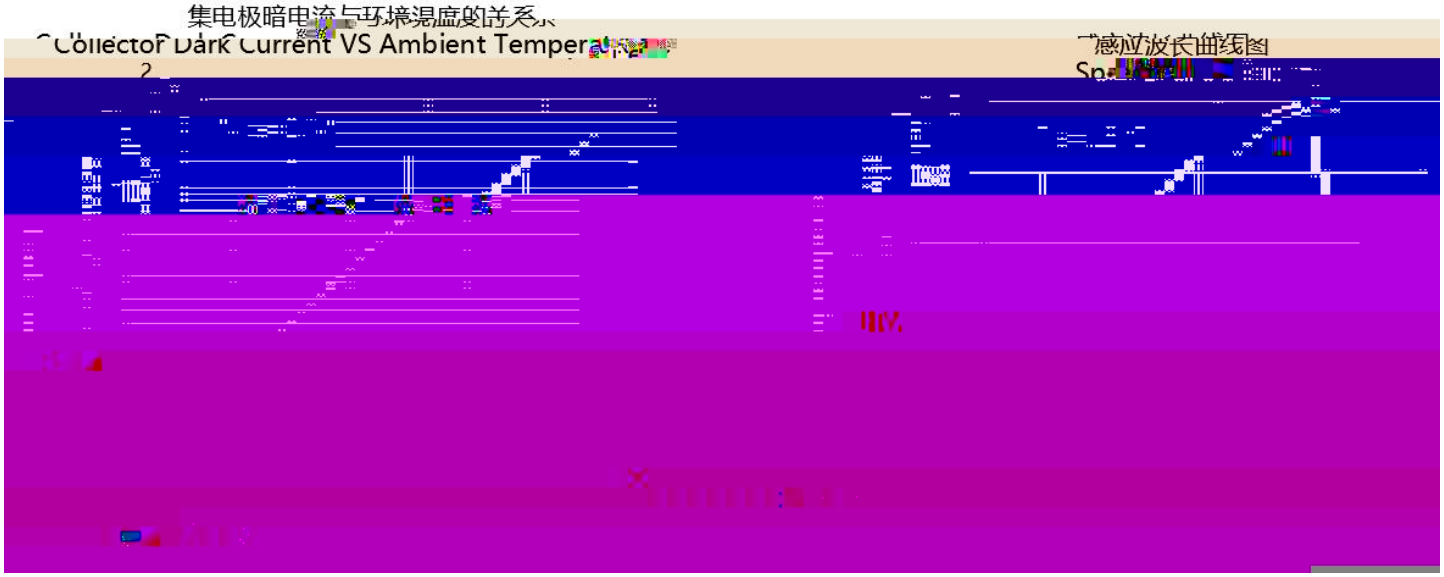
Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
FoĎ						
Input						

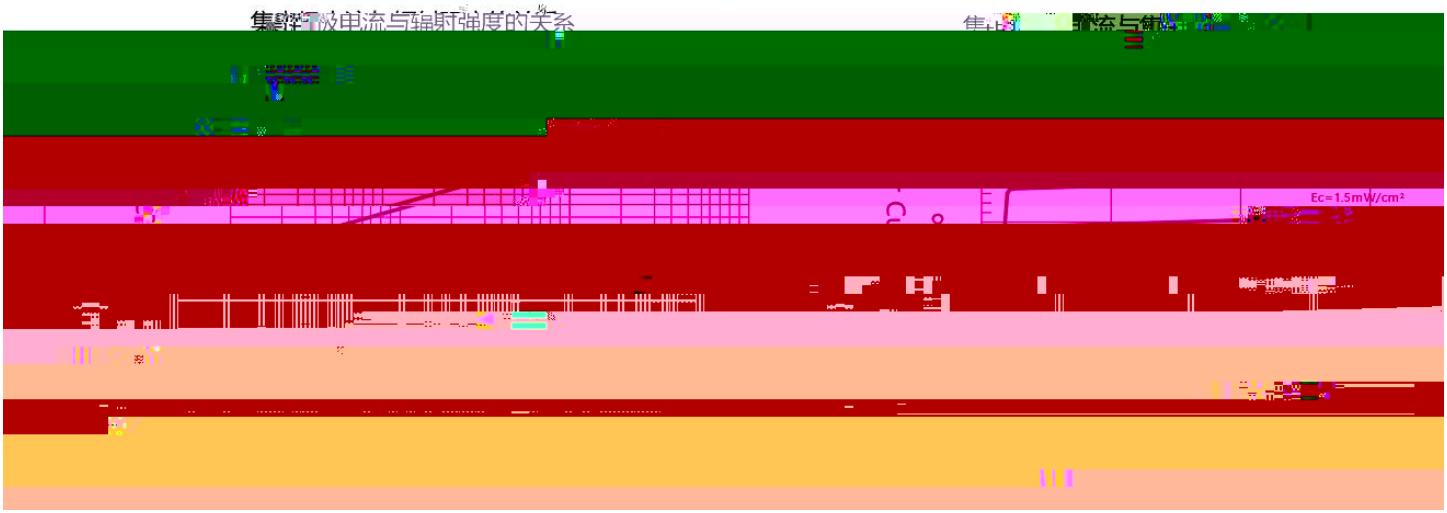
电压公差

典型特性曲线

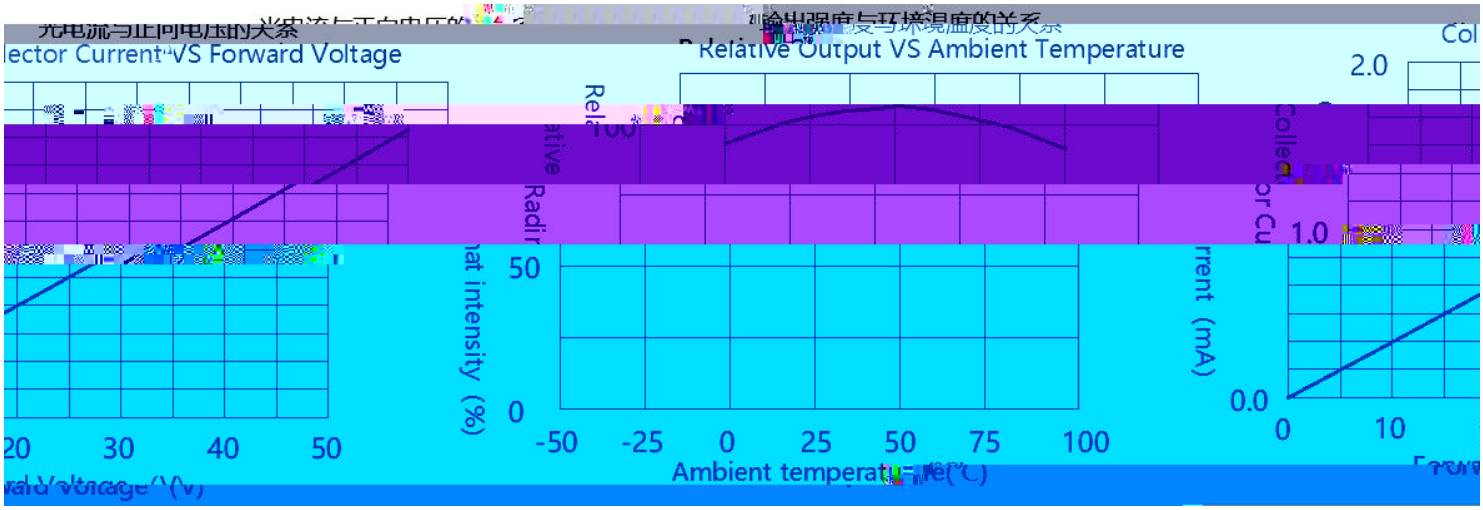
Typical Charactere

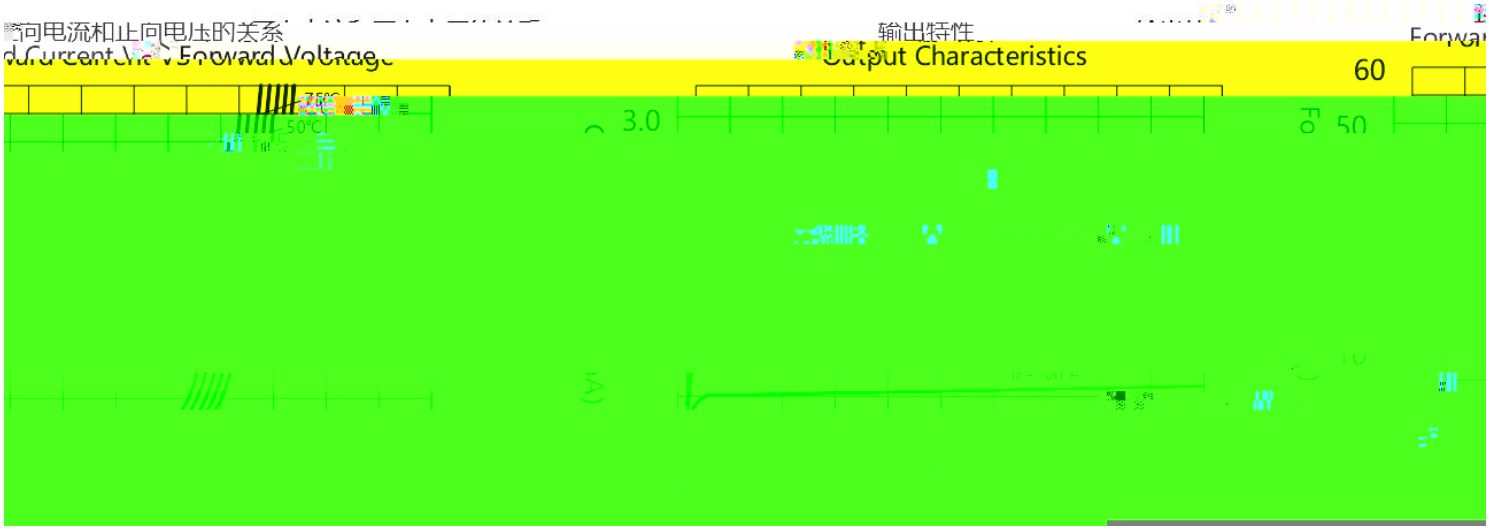
接收管特性曲线图 Typical Electro-Optical Characteristics Curves-PT





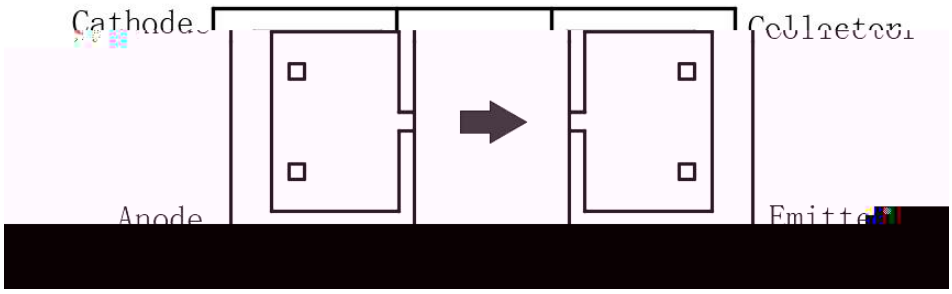
光电开关特性曲线图 Typical Electro-Optical Characteristics Curves-I





外形尺寸

Outline Dimension



1. mm

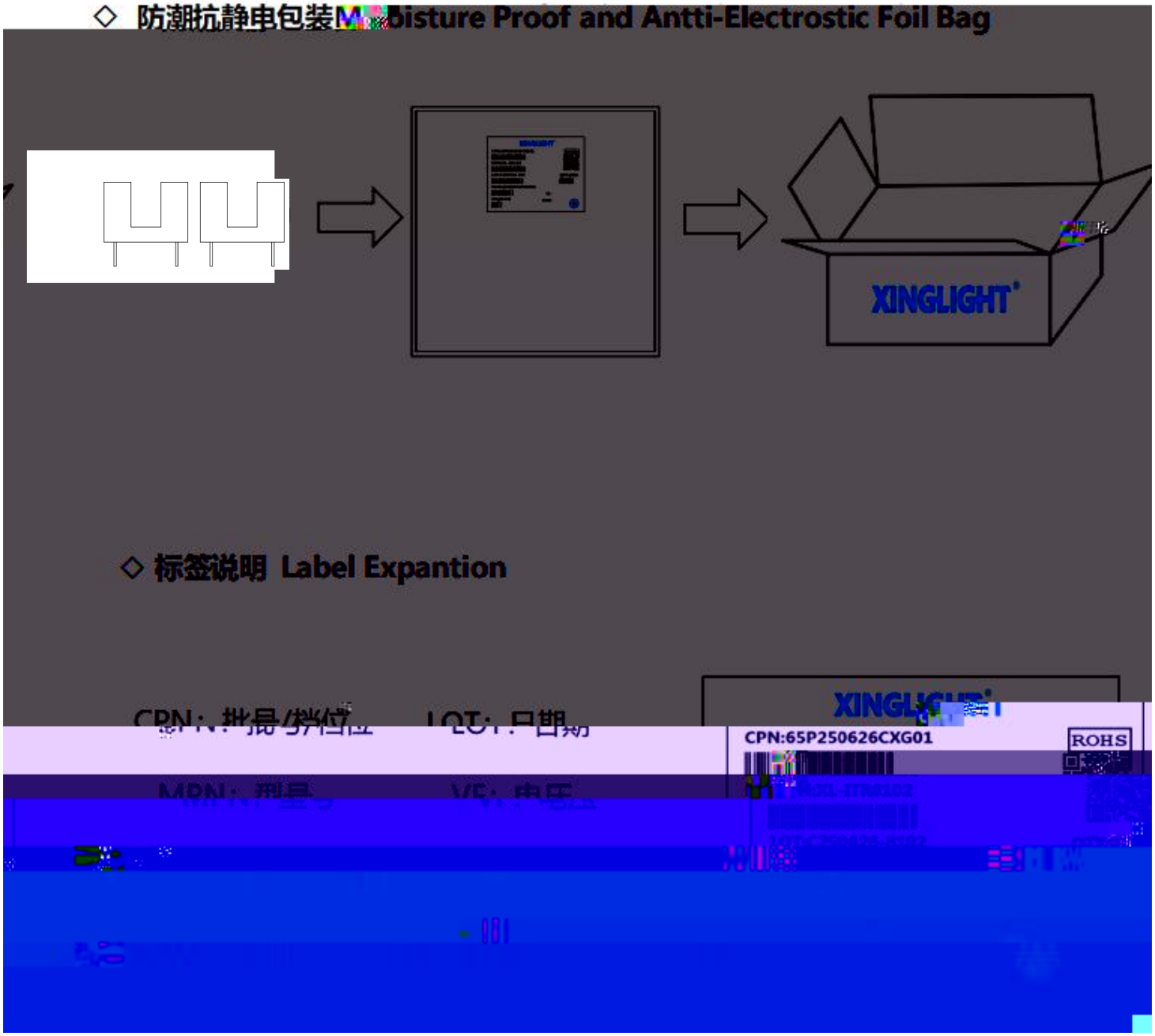
Remarks: 1 Unit: mm

2. Ñ0.3mm

2. Tolerance: Ñ 0.3mm unless otherwise specified

包装

Packaging



Guideline for Soldering

The wave peak welding curve is recommended :

使用注意事項

Precautions

NPN

IR

IR PT

This product It is composed of infrared emission diode and NPN silicon photo transistor, which are packaged side by side in black On the converging optical axis in the thermoplastic shell. Photo transistor only receives radiation from IR. This is normal Condition. But when the object is in the middle, the photo transistor cannot receive radiation. For more component information, please Refer to IR and PT.